

Silicon Transistors

	Type No.	Case	Construction (see note 1)	Maximum Ratings at 25°C amb.					Characteristics									SPECIAL FEATURES
				V _{CB} V	V _{CE} V	V _{EB} V	I _C A	P _{tot} W	h _{FE}			f _T		V _{CE(SAT)}				
									I _C mA	Min.	Max.	I _C mA	Min. Mc/s	I _C mA	I _B mA	Max. V		
NPN High Frequency Amplifiers	2N915	TO18	P	70	50	5	0.10	0.36	10	50	200	10	250	10	1	1.0		
	2N916	TO18	PE	45	25	5	0.10	0.36	10	50	200	10	300	10	1	0.5		
	2N918	TO72	PE	30	15	3	0.05	0.2	3	20	—	4	600	10	1	0.4		
	2N2865	TO72	PE	25	13	3	0.05	0.2	4	20*	200*	4	600	10	1	0.4		
	2S102	TO18	P	60	45	6	0.05	0.40	5	20*	50*	5	150	10	2.0	1.0		
	2S103	TO18	P	60	45	6	0.05	0.40	5	40*	100*	5	150	10	2.0	1.0		
	2S104	TO18	P	60	45	6	0.05	0.40	5	80*	200*	5	150	10	2.0	1.0		
	2S731	TO18	P	30	30	4.5	0.05	0.40	5	20*	50*	5	30.0	10	2.0	1.0		
	2S732	TO18	P	30	30	4.5	0.05	0.40	5	40*	100*	5	30.0	10	2.0	1.0		
	2S733	TO18	P	30	30	4.5	0.05	0.40	5	80*	200*	5	30.0	10	2.0	1.0		
	TIS18	Silect	P	25	13	3	0.03	0.20	10	20	—	10	600	—	—	—	(TI407)	
	2N3983	Silect	P	30	12	3	0.03	0.20	4	30	—	4	500	—	—	—	(TI408)	
	2N3984	Silect	P	30	12	3	0.03	0.20	4	20	—	4	400	—	—	—	(TI409)	
	2N3985	Silect	P	30	12	3	0.03	0.20	4	20	—	4	300	—	—	—		
	2N3825	Silect	PE	30	15	4	0.10	0.25	2	20	—	2	200	2	0.2	0.25		
	2N3826	Silect	P	60	45	4	0.03	0.20	10	40	160	10	200	—	—	—		
	2N3827	Silect	P	60	45	4	0.03	0.20	10	100	400	10	200	—	—	—		
	2N4254	Silect	PE	30	18	4	0.05	0.20	2	50	—	2	600	—	—	—		
2N4255	Silect	PE	30	18	4	0.05	0.20	2	30	150	2	600	—	—	—			
BF224	Silect	PE	45	30	4	0.05	0.36	7	30	—	1.0	300	10	1.0	0.25	^C 12e 0.23 pf Typ.		
BF225	Silect	PE	50	40	4	0.05	0.36	4	30	—	4.0	400	—	—	—	A.G.C. DEVICE		
NPN UHF Amplifiers	2N3570	TO72	PE	30	15	3	0.05	0.20	5	20	150	5	1500	—	—	—	N.F. < 7dB at 1000 Mc/s	
	2N3571	TO72	PE	25	15	3	0.05	0.20	5	20	200	5	1200	—	—	—	N.F. < 4dB at 400 Mc/s	
	2N3572	TO72	PE	25	13	3	0.05	0.20	5	20	300	5	1000	—	—	—	N.F. < 6dB at 400 Mc/s	
PNP High Frequency Amplifiers	TIS37	Silect	P	-35	-32	-6	0.05	0.20	-1	45	—	-1	80	—	—	—		
	TIS38	Silect	P	-35	-32	-4	0.05	0.20	-1	25	—	-1	50	—	—	—		
NPN High Frequency Medium Power	2N2217	TO5	PE	60	30	5	0.8	0.8	150	20	60	20	250	150	15	0.4	Total switching time < 80nS at 150 mA Po > 0.5 W at 500 Mc Po > 0.75 W at 500 Mc	
	2N2218	TO5	PE	60	30	5	0.8	0.8	150	40	120	20	250	150	15	0.4		
	2N2219	TO5	PE	60	30	5	0.8	0.8	150	100	300	20	250	150	15	0.4		
	2N2220	TO18	PE	60	30	5	0.8	0.5	150	20	60	20	250	150	15	0.4		
	2N2221	TO18	PE	60	30	5	0.8	0.5	150	40	120	20	250	150	15	0.4		
	2N2222	TO18	PE	60	30	5	0.8	0.5	150	100	300	20	250	150	15	0.4		
	2N2537	TO5	PE	60	30	5	0.8	0.8	150	50	150	20	250	150	15	0.45		
	2N2538	TO5	PE	60	30	5	0.8	0.8	150	100	300	20	250	150	15	0.45		
	2N2539	TO18	PE	60	30	5	0.8	0.5	150	50	150	20	250	150	15	0.45		
	2N2540	TO18	PE	60	30	5	0.8	0.5	150	100	300	20	250	150	15	0.45		
	2N2883	TO5	PE	40	20	4	0.3	0.8	100	20	—	50	400	100	10	0.5		
	2N2884	TO5	PE	40	20	4	0.3	0.8	100	20	—	50	400	100	10	0.5		
	2N3704	Silect	PE	50	30	5	0.8	0.36	50	100	300	50	100	100	5	0.6		
	2N3705	Silect	PE	50	30	5	0.8	0.36	50	50	150	50	100	100	5	0.8		
	2N3706	Silect	PE	40	20	5	0.8	0.36	50	30	600	50	100	100	5	1.0		

NOTE 1: The following symbols have been used throughout the Product Summary:

Under "Construction":

A — Alloyed
D — Diffused
E — Epitaxial
G — Grown
M — Mesa
P — Planar

Under h_{FE}:

* — h_{fe}

Under f_T:

φ — f_{hfb}
Δ — f_{hfe}
‡ — typical

Under Dissipation:

† — dissipation at T_{case} = 25°C